Application No.: 10/748,721 Docket No.: 29936/39851

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of forming a metal line of a semiconductor device, comprising the steps of:

forming an interlayer insulating film on a semiconductor substrate;

forming a metal line shaped pattern by etching the interlayer insulating film;

forming a diffusion stopper film in conformity with a whole surface of a resultant material in which the metal line shaped pattern is formed;

forming a copper film on the diffusion stopper film;

forming a copper metal line by chemically and mechanically polishing the copper film and the diffusion stopper film above the interlayer insulating film;

selectively attaching a titanium metal or a ruthenium metal to only the copper metal line selectively; and

annealing the attached titanium metal or ruthenium metal.

- 2. (Canceled)
- 3. (Original) The method according to Claim 1, wherein the step of attaching the titanium metal is performed by dipping the copper metal line into a solution containing titanium chloride (TiCl₄) and hypo-phosphorous acid (H₃PO₂).

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4. (Currently Amended) The method according to Claim 1, wherein the annealing step is performed under an atmosphere containing nitrogen (N₂), hydrogen (H₂), or argon (Ar) gases, at a temperature of 200°C to 400°C, and for 1 hour to 3 hours.

- 5. (Original) The method according to Claim 1, further comprising a step of forming a capping film after the annealing step.
- 6. (Original) The method according to Claim 1, wherein the capping film is formed of a silicon nitride film (Si_3N_4) or a silicon carbide film (SiC).